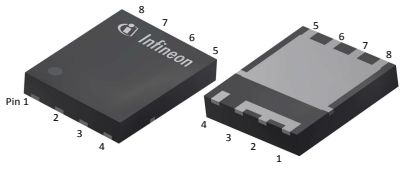
MOSFET

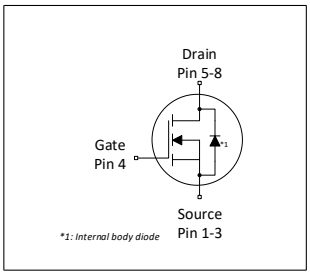
OptiMOS™ 6 Power-Transistor, 100 V

PG-TSON-8-3



Features

- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low reverse recovery charge (Q_{rr})
- High avalanche energy rating
- 175°C operating temperature
- Optimized for high frequency switching and synchronous rectification
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- MSL 1 classified according to J-STD-020



Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	2.24	mΩ
I_D	230	A
Q_{oss}	135	nC
Q_G(0V...10V)	73	nC
Q_{rr} (100A/µs)	70	nC

Type / Ordering Code	Package	Marking	Related Links
ISC022N10NM6	PG-TSON-8	022N1N6	-

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - -	- - - -	230 163 147 25	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=8 V, T_C=100 °C V_{GS}=10 V,T_A=25°C, R_{thJA}=50°C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	920	A	T_A=25 °C
Avalanche current, single pulse[4]	I_{AS}	-	-	50	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	1535	mJ	I_D=21 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	254 3.0	W	T_C=25 °C T_A=25 °C, R_{thJA}=50 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.29	0.59	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	°C/W	-
Thermal resistance, junction - ambient, 6 cm² cooling area	R_{thJA}	-	-	50	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.3	2.8	3.3	V	V_{DS}=V_{GS}, I_D=147 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1.0 100	µA	V_{DS}=80 V, V_{GS}=0 V, T_j=25 °C V_{DS}=80 V, V_{GS}=0 V, T_j=125 °C[1)]
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	1.8 2.2	2.24 2.7	mΩ	V_{GS}=10 V, I_D=50 A V_{GS}=8 V, I_D=25 A
Gate resistance	R_G	0.7	1.4	2.1	Ω	-
Transconductance	g_{fs}	48.5	97	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=50 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	5400	6880	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	1200	1500	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	19	28	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	13	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=25 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	6	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=25 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	30	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=25 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	7	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=25 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge[1)]	Q_{gs}	-	24	32	nC	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Gate charge at threshold[1)]	$Q_{g(th)}$	-	15.1	19	nC	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Gate to drain charge[1)]	Q_{gd}	-	11.9	18	nC	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	21	-	nC	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Gate charge total[1)]	Q_g	-	73	91	nC	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.4	-	V	V_{DD}=50 V, I_D=25 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	67	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 10 V
Output charge[1)]	Q_{oss}	-	135	169	nC	V_{DS}=50 V, V_{GS}=0 V

[1)] Defined by design. Not subject to production test.
[2)] See ″Gate charge waveforms″ for parameter definition

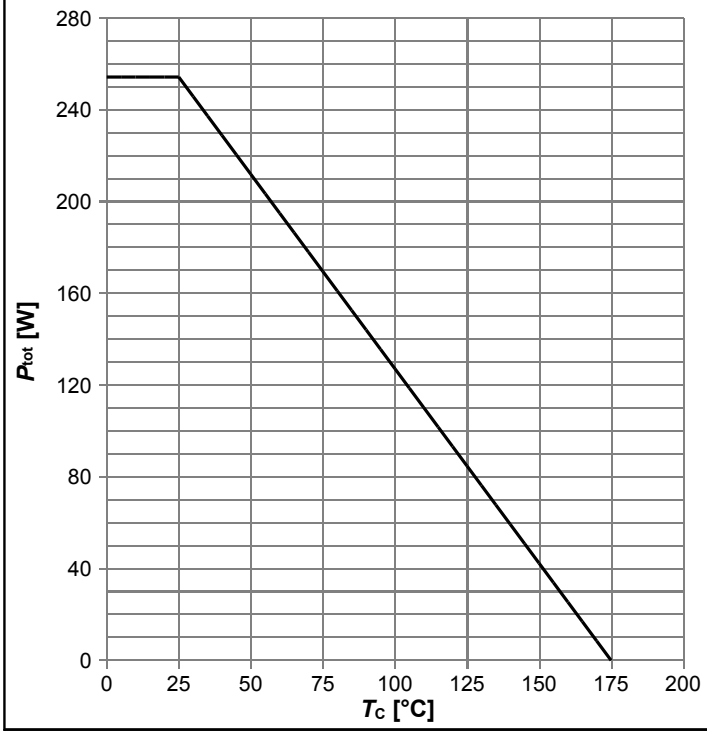
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	212	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	920	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.80	1.0	V	V_{GS}=0 V, I_F=50 A, T_j=25 °C
Reverse recovery time[1)]	t_{rr}	-	52	78	ns	V_R=50 V, I_F=25 A, di_F/dt=100 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	70	105	nC	V_R=50 V, I_F=25 A, di_F/dt=100 A/µs
Reverse recovery time[1)]	t_{rr}	-	28	42	ns	V_R=50 V, I_F=25 A, di_F/dt=1000 A/µs
Reverse recovery charge[1)]	Q_{rr}	-	325	488	nC	V_R=50 V, I_F=25 A, di_F/dt=1000 A/µs

[1)] Defined by design. Not subject to production test.

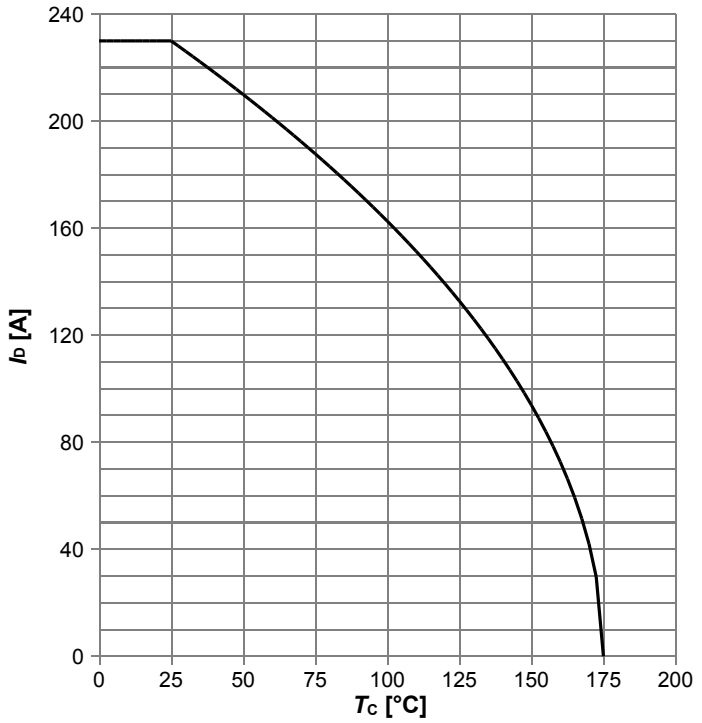
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



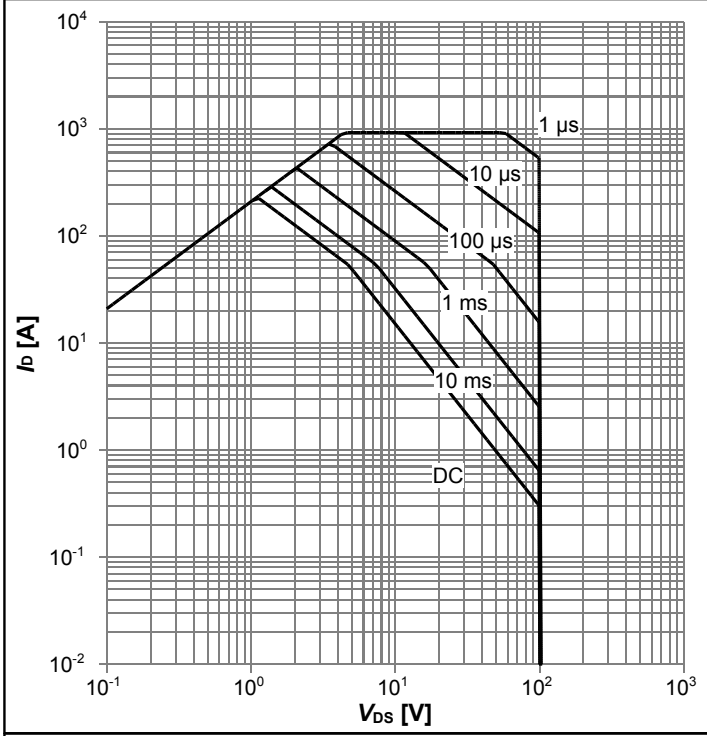
$P_{tot}=f(T_C)$

Diagram 2: Drain current



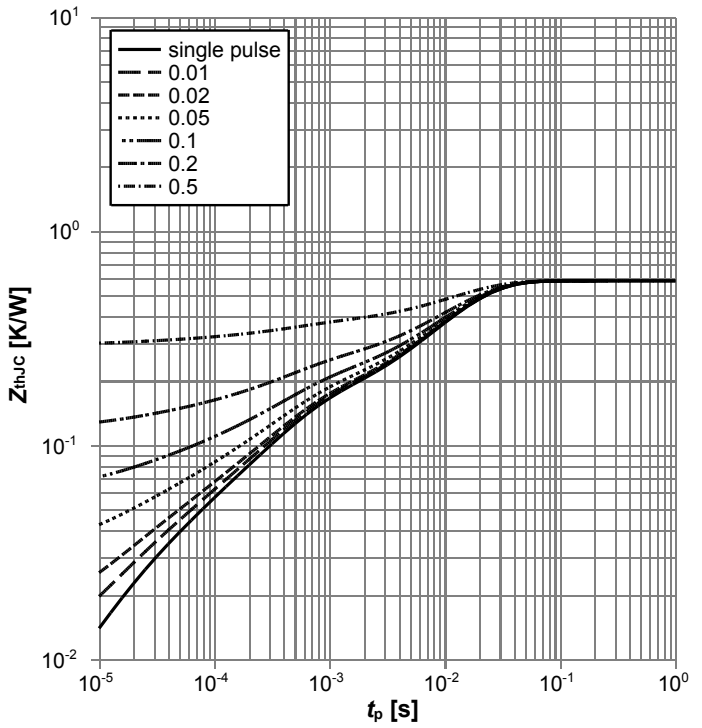
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



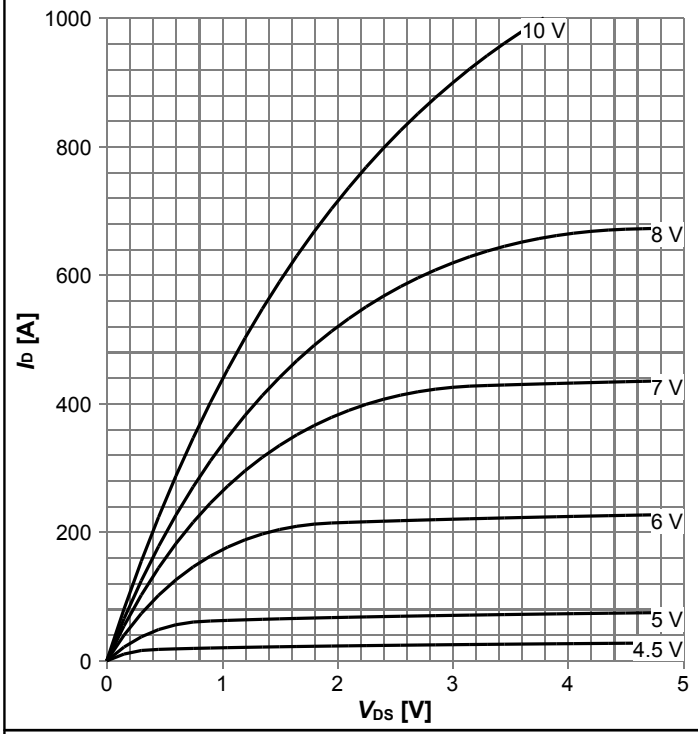
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



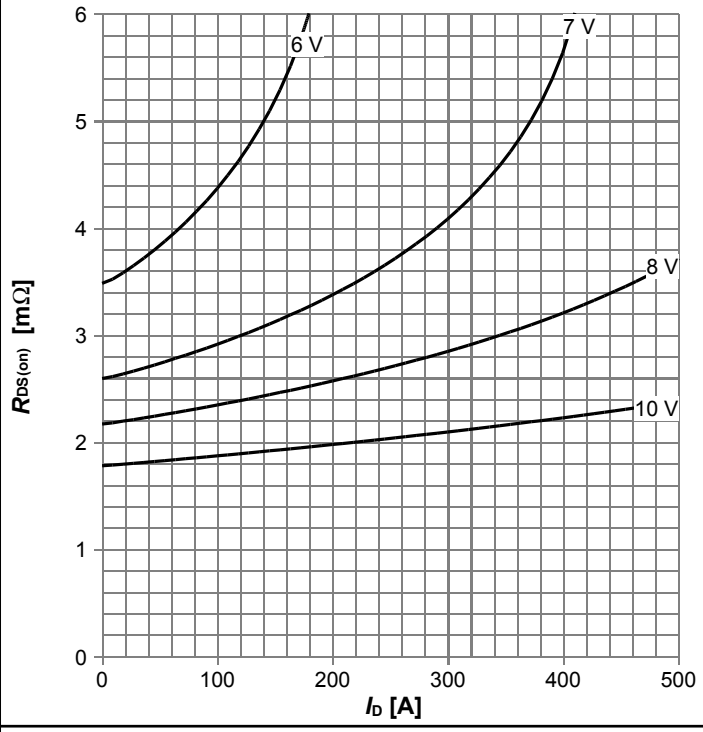
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



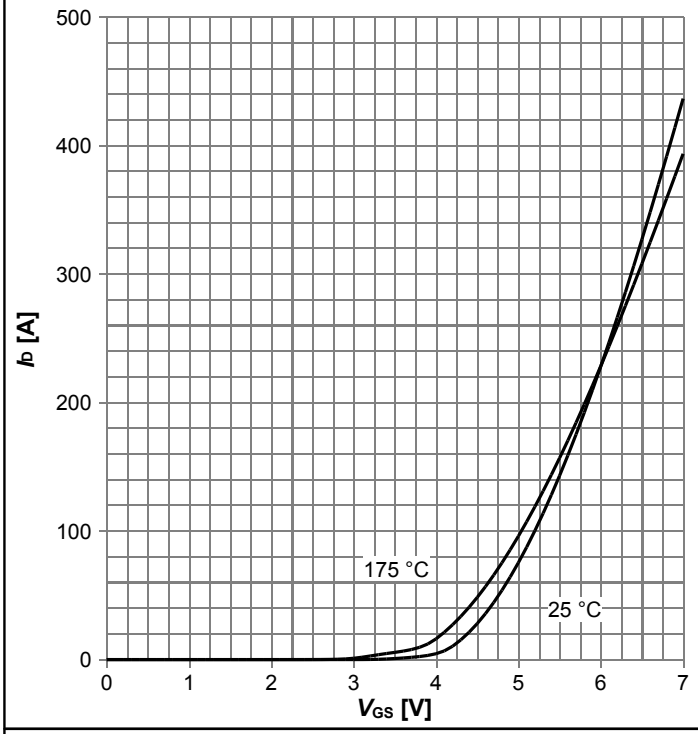
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



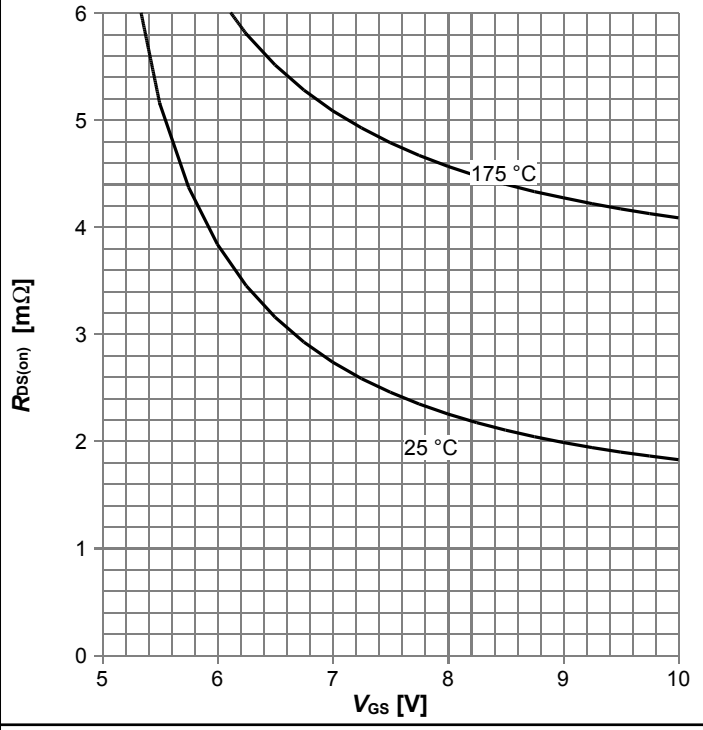
$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



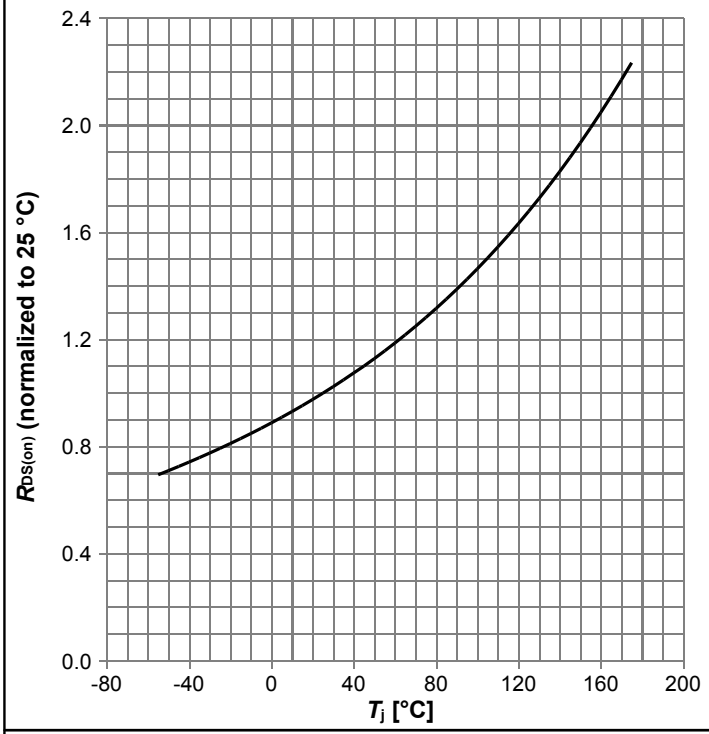
I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



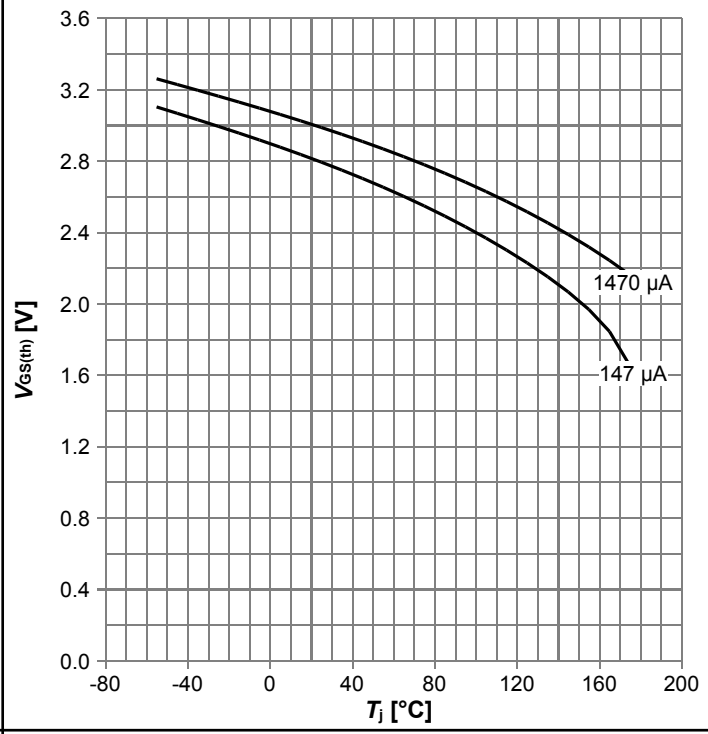
$R_{DS(on)}$=f(V_{GS}), I_D=50 A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



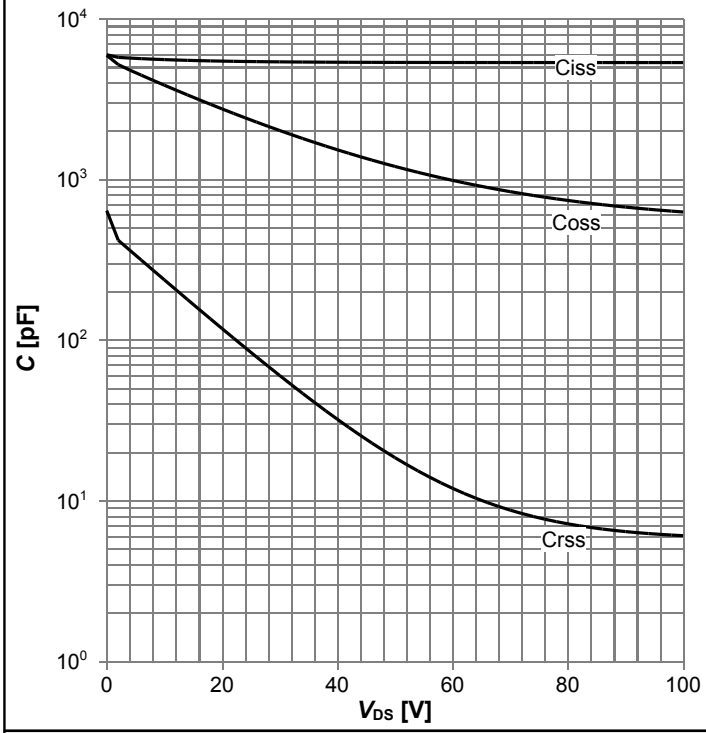
$R_{DS(on)}$=f(T_j), I_D=50 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



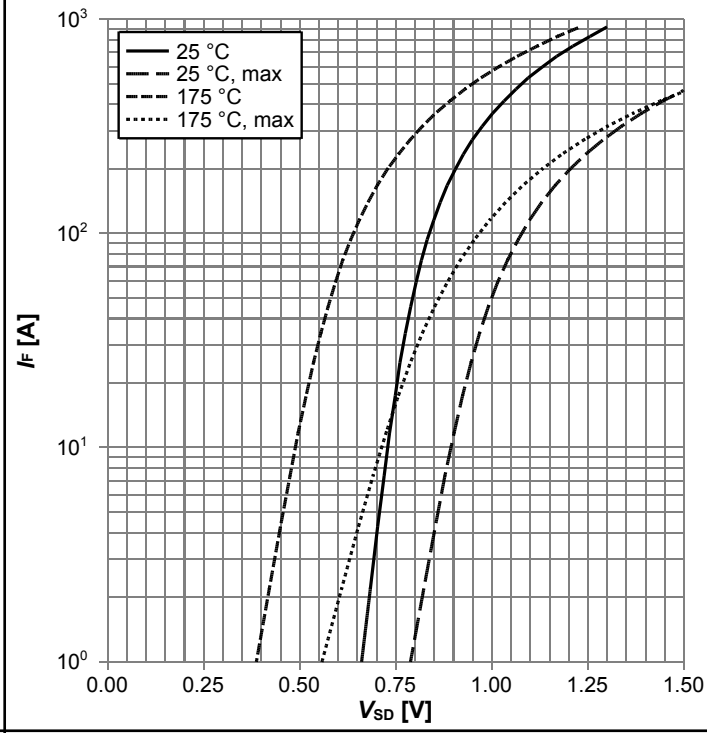
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



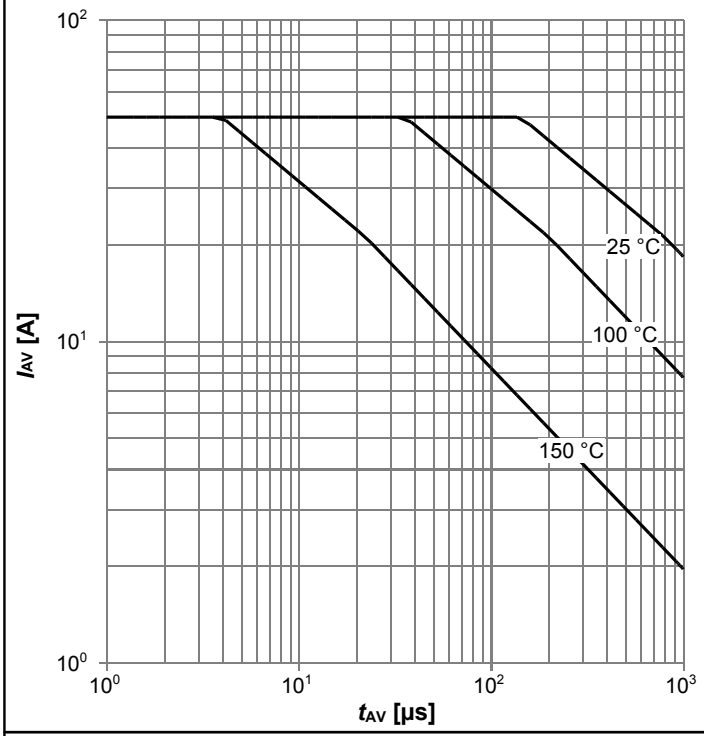
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



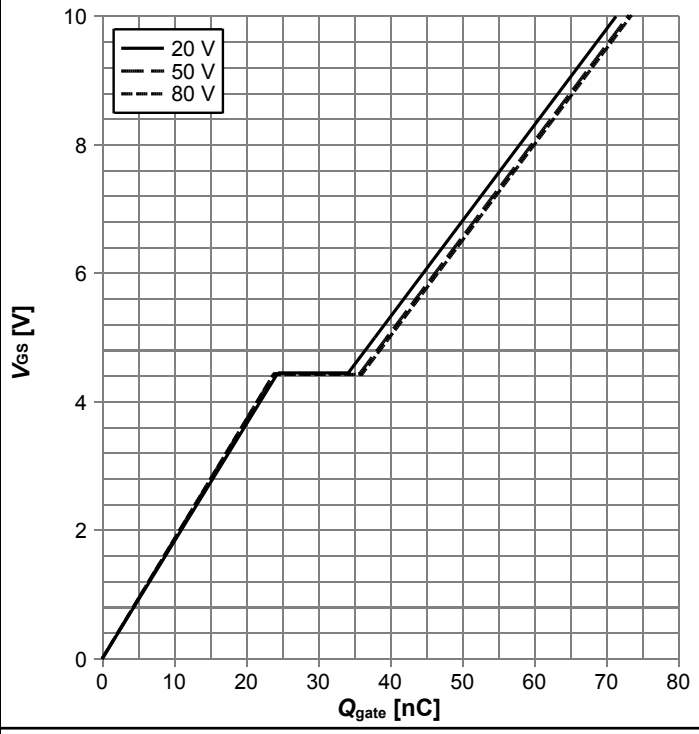
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



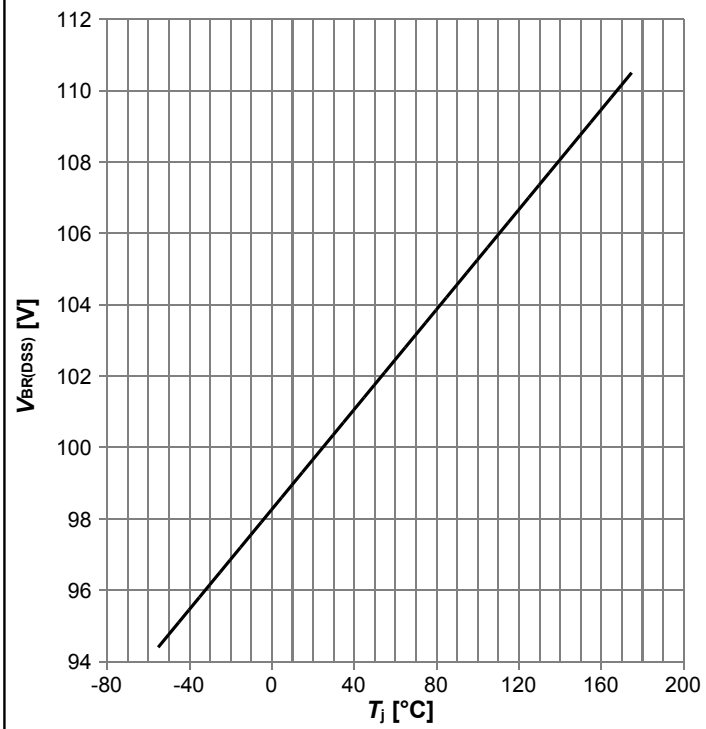
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



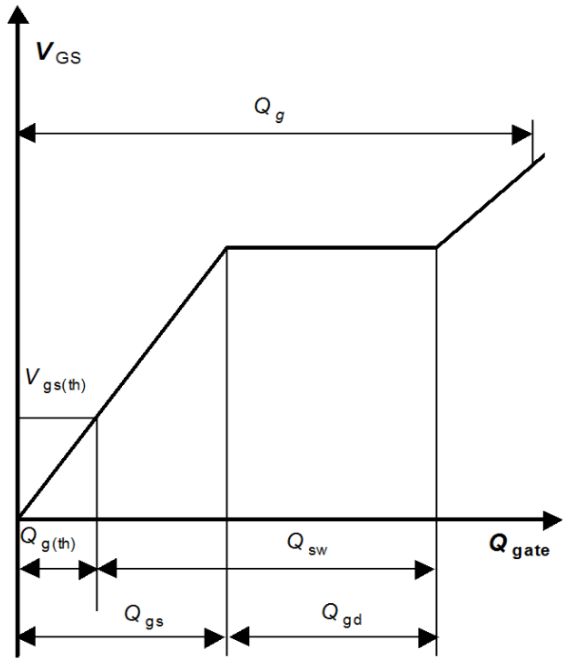
V_{GS}=f(Q_{gate}), I_D=25 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

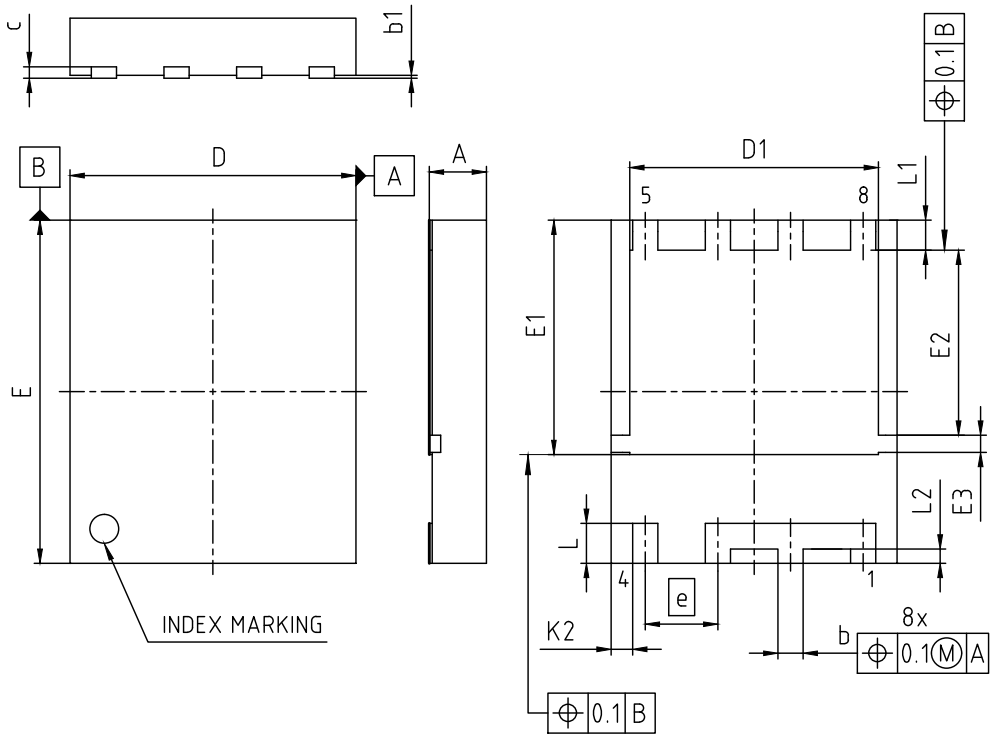


$V_{BR(DSS)}$=f(T_j); I_D=10 mA

Diagram Gate charge waveforms



5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
b	0.34	0.54
b1	-	0.05
c	0.20	
D	4.90	5.10
D1	4.25	4.45
E	5.90	6.10
E1	4.00	4.20
E2	3.14	3.34
E3	0.20	0.40
e	1.27	
K2	(0.37)	
L	0.60	0.80
L1	0.43	0.63
L2	(0.25)	

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Figure 1 Outline PG-TSON-8, dimensions in mm/inches

Revision History

ISC022N10NM6

Revision: 2023-02-14, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2021-07-05	Release of final version
2.1	2023-02-14	Update SOA Diagram

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